



# L660-06N

For Plant Growth and Photo Synthetically Active Radiation use

L660-06N is an AlGaInP LED mounted on a lead frame with a clear epoxy lens.

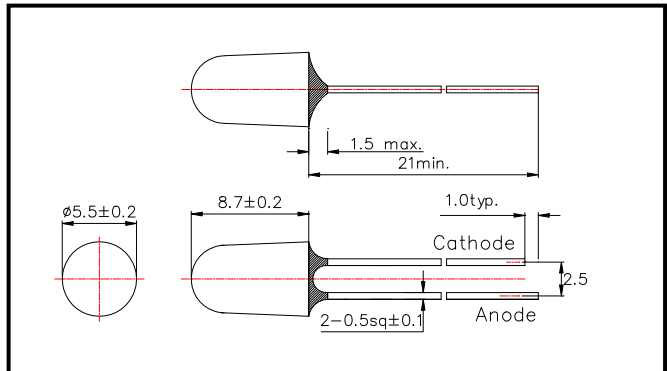
This is designed for the highest Po and dampproof.

On forward bias it emits a band of visible light, which peaks 660nm.

### ◆ Specifications

- 1) Product Name      Red LED Lamp
- 2) Type No.          L660-06N
- 3) Chip
- (1) Chip Material      AlGaInP
- (2) Peak Wavelength   660nm typ.
- 4) Package
- (1) Type                Φ5mm clear molding
- (2) Resin Material      Epoxy Resin
- (3) Lead Frame        Soldered

### ◆ Outer dimension (Unit: mm)



### ◆ Absolute Maximum Ratings

Item	Symbol	Maximum Rated Value	Unit	Ambient Temperature
Power Dissipation	P <sub>D</sub>	130	mW	T <sub>a</sub> =25°C
Forward Current	I <sub>F</sub>	50	mA	T <sub>a</sub> =25°C
Reverse Voltage	V <sub>R</sub>	5	V	T <sub>a</sub> =25°C
Operating Temperature	T <sub>OPR</sub>	-30 ~ +80	°C	
Storage Temperature	T <sub>STG</sub>	-30 ~ +100	°C	
Soldering Temperature	T <sub>SOL</sub>	265	°C	

‡Soldering condition: Soldering condition must be completed within 3 seconds at 265°C

### ◆ Electro-Optical Characteristics

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	V <sub>F</sub>	I <sub>F</sub> =20mA		2.15	2.40	V
Reverse Current	I <sub>R</sub>	V <sub>R</sub> =5V			10	uA
Total Radiated Power	P <sub>O</sub>	I <sub>F</sub> =20mA	12	18		mW
Radiant Intensity	I <sub>E</sub>	I <sub>F</sub> =50mA		110		mW/sr
Brightness	I <sub>V</sub>	I <sub>F</sub> =20mA		5500		mcd
Peak Wavelength	λ <sub>P</sub>	I <sub>F</sub> =20mA	650	660	670	nm
Half Width	Δλ	I <sub>F</sub> =20mA		18		nm
Viewing Half Angle	θ <sub>1/2</sub>	I <sub>F</sub> =20mA		±6		deg.

‡Brightness is measured by Tektronix J-16.

‡Total Radiated Power is measured by Photodyne #500